

2010:

M. F. Beug, T. Melde, M. Czernohorsky, R. Hoffmann, J. Paul, R. Knöfler, and A. T. Tilke, "Analysis of TANOS memory cells with sealing oxide containing blocking dielectric," *IEEE Transactions on Electron Devices*, vol. 57, no. 7, pp. 1590–1596, Jul. 2010.

[7]

C. Chèze, L. Geelhaar, O. Brandt, W. Weber, H. Riechert, S. Münch, R. Rothemund, S. Reitzenstein, A. Forchel, T. Kehagias, P. Komninou, G. Dimitrakopoulos, and T. Karakostas, "Direct comparison of catalyst-free and catalyst-induced GaN nanowires," *Nano Research*, vol. 3, no. 7, pp. 528–536, 2010.

[8]

A. P. Graham, K. Richter, T. Jay, W. Weber, S. Knebel, U. Schröder, and T. Mikolajick, "An investigation of the electrical properties of metal-insulator-silicon capacitors with pyrolytic carbon electrodes," *Journal of Applied Physics*, vol. 108, pp. 104508–104508–4, Nov. 2010.

[9]

A. P. Graham, G. Schindler, G. S. Duesberg, T. Lutz, and W. Weber, "An investigation of the electrical properties of pyrolytic carbon in reduced dimensions: Vias and wires," *Journal of Applied Physics*, vol. 107, no. 11, pp. 114316–114316–4, Jun. 2010.

[10]

G. Jegert, A. Kersch, W. Weinreich, U. Schröder, and P. Lugli, "Modeling of leakage currents in high- κ dielectrics: Three-dimensional approach via kinetic Monte Carlo," *Applied Physics Letters*, vol. 96, no. 6, pp. 062113–062113–3, Feb. 2010.

[11]

S. Schmelzer, D. Bräuhäus, S. Hoffmann-Eifert, P. Meuffels, U. Böttger, L. Oberbeck, P. Reinig, U. Schröder, and R. Waser, "SrTiO₃ thin film capacitors on silicon substrates with insignificant interfacial passive layers," *Applied Physics Letters*, vol. 97, no. 13, pp. 132907–132907–3, Sep. 2010.

[12]

D. Zhou, U. Schröder, J. Xu, J. Heitmann, G. Jegert, W. Weinreich, M. Kerber, S. Knebel, E. Erben, and T. Mikolajick, "Reliability of Al₂O₃-doped ZrO₂ high-k dielectrics in three-dimensional stacked metal-insulator-metal capacitors," *Journal of Applied Physics*, vol. 108, no. 12, pp. 124104–124104–5, Dec. 2010.

[13]